AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the present application.

Listing of Claims:

Claim 1 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment, the ceramic susceptor comprising:

a ceramic substrate, one side thereof having a wafer-retaining face;

a resistive heating element provided either superficially or interiorly in said substrate; and

a recess formed in said wafer-retaining face with room to carry a semiconductor manufacturing wafer, said recess including a perimetric wall and a substantially planar bottom face, and being shaped such that the perimetric wall meets the bottom face to form an angle greater than 90° and less than 170°, the bottom face being sized to receive a back side of the wafer such that the back side is in contact with the bottom face across substantially the entire diameter of the wafer.

Claim 2 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said ceramic substrate is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 3 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 4 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 2, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 5 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 6 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 2, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 7 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 3, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 8 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 4, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 9 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said recess is further shaped so that the perimetric wall and the bottom face join in a bottom-portion circumferential verge having a curvature of 0.1 mm or more.

Claim 10 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said ceramic substrate

is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 11 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 12 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 13 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 14 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 15 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 11, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 16 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 12, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 17 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment, the ceramic susceptor comprising:

a ceramic substrate, one side thereof having a wafer-retaining face;

a resist<u>ive</u>[[ed]] heating element provided either superficially [[more]] <u>or</u> interiorly in said substrate; and

a recess formed in said wafer-retaining face with room to carry a semiconductor manufacturing wafer, the recess including a perimetric wall and a bottom face, the perimetric wall and the bottom face joining in a circumferential verge having a radius of curvature of [[a]] 0.1 mm or more<u>, the bottom face being sized to receive a back side of the wafer such that the back side is in contact with the bottom face across substantially the entire diameter of the wafer</u>.

Claim 18 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said ceramic substrate is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 19 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 20 (previously presented): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.